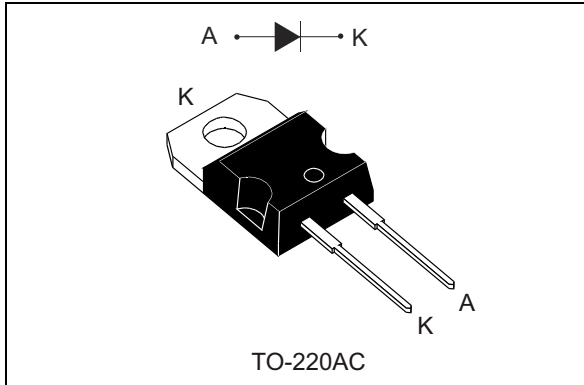


650 V power Schottky silicon carbide diode

Datasheet - production data



Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

Table 1. Device summary

| Symbol | Value |
|-------------|--------|
| $I_{F(AV)}$ | 12 A |
| V_{RRM} | 650 V |
| T_j (max) | 175 °C |

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified)

| Symbol | Parameter | | Value | Unit |
|--------------|---|--|-------------|------|
| V_{RRM} | Repetitive peak reverse voltage | | 650 | V |
| $I_{F(RMS)}$ | Forward rms current | | 22 | A |
| $I_{F(AV)}$ | Average forward current | $T_c = 130\text{ °C}^{(1)}, \delta = 0.5$ | 12 | A |
| I_{FSM} | Surge non repetitive forward current | $t_p = 10\text{ ms sinusoidal}, T_c = 25\text{ °C}$ | 100 | A |
| | | $t_p = 10\text{ ms sinusoidal}, T_c = 125\text{ °C}$ | 90 | |
| | | $t_p = 10\text{ }\mu\text{s square}, T_c = 25\text{ °C}$ | 400 | |
| I_{FRM} | Repetitive peak forward current | $T_c = 130\text{ °C}^{(1)}, T_j = 150\text{ °C}, \delta = 0.1$ | 50 | A |
| T_{stg} | Storage temperature range | | -55 to +175 | °C |
| T_j | Operating junction temperature ⁽²⁾ | | -40 to +175 | °C |

- Value based on $R_{th(j-c)}$ max.
- $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance

| Symbol | Parameter | Value | | Unit |
|---------------|------------------|-------|------|------|
| | | Typ. | Max. | |
| $R_{th(j-c)}$ | Junction to case | 1.00 | 1.4 | °C/W |

Table 4. Static electrical characteristics

| Symbol | Parameter | Tests conditions | Min. | Typ. | Max. | Unit | |
|-------------|-------------------------|-----------------------|---------------------|------|------|------|---------------|
| $I_R^{(1)}$ | Reverse leakage current | $T_j = 25\text{ °C}$ | $V_R = V_{RRM}$ | - | 10 | 120 | μA |
| | | $T_j = 150\text{ °C}$ | | - | 100 | 500 | |
| $V_F^{(2)}$ | Forward voltage drop | $T_j = 25\text{ °C}$ | $I_F = 12\text{ A}$ | - | 1.56 | 1.75 | V |
| | | $T_j = 150\text{ °C}$ | | - | 1.98 | 2.5 | |

- $t_p = 10\text{ ms}, \delta < 2\%$
- $t_p = 500\text{ }\mu\text{s}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.096 \times I_{F(RMS)}^2$$

Table 5. Dynamic electrical characteristics

| Symbol | Parameter | Test conditions | Typ. | Unit |
|----------------|-------------------------|--|------|------|
| $Q_{cj}^{(1)}$ | Total capacitive charge | $V_R = 400\text{ V},$ | 36 | nC |
| C_j | Total capacitance | $V_R = 0\text{ V}, T_c = 25\text{ °C}, F = 1\text{ MHz}$ | 600 | pF |
| | | $V_R = 400\text{ V}, T_c = 25\text{ °C}, F = 1\text{ MHz}$ | 60 | |

- Most accurate value for the capacitive charge: $Q_{cj} = \int_0^{V_{OUT}} c_j(v_R).dv_R$

Figure 1. Forward voltage drop versus forward current (typical values, low level)

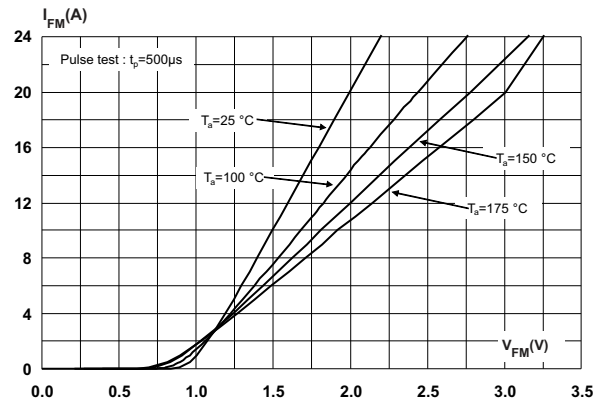


Figure 2. Forward voltage drop versus forward current (typical values, high level)

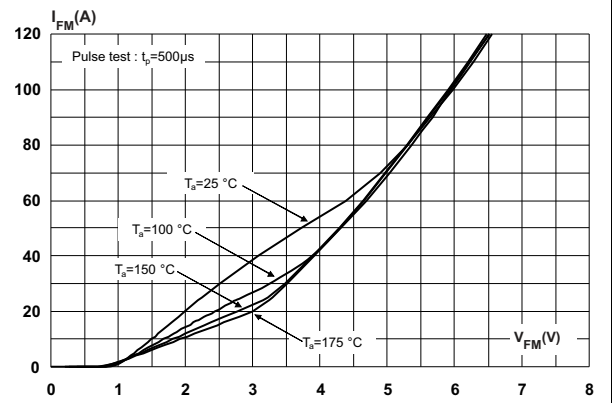


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

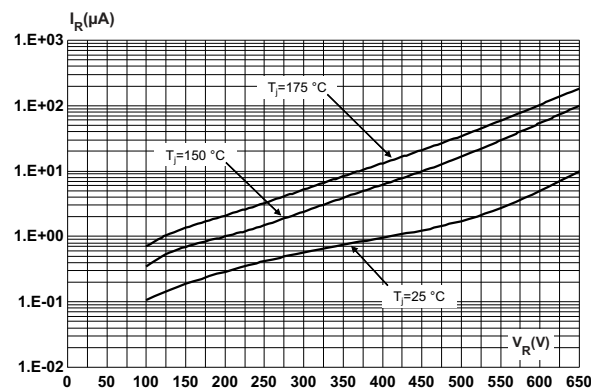


Figure 4. Peak forward current versus case temperature

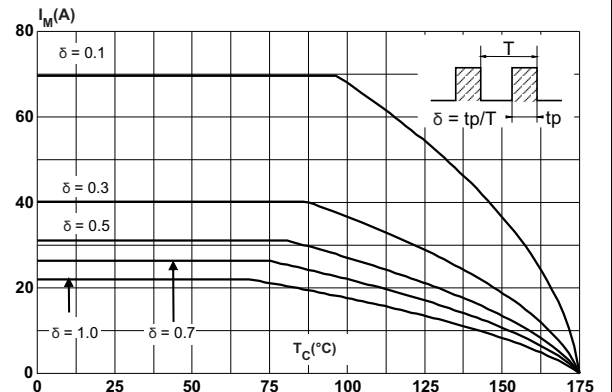


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

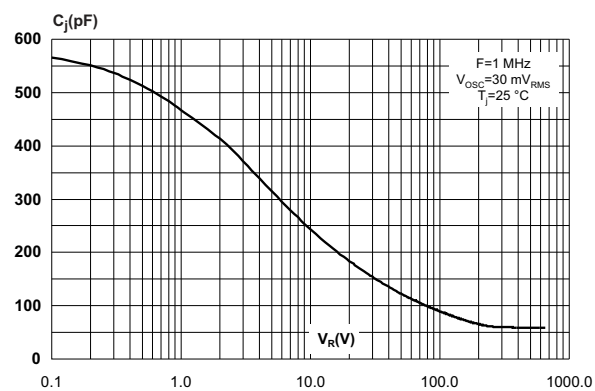


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration

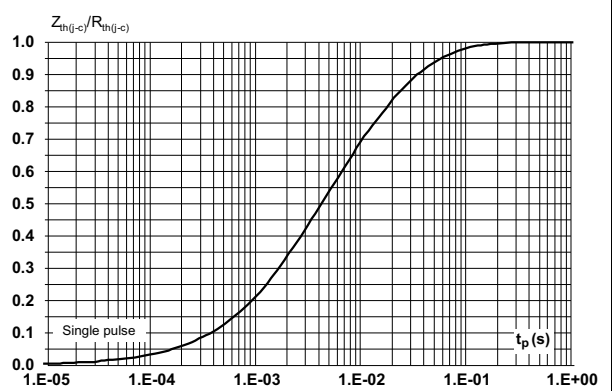


Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

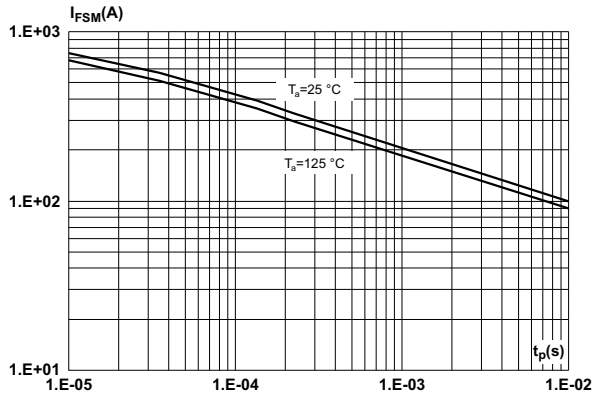
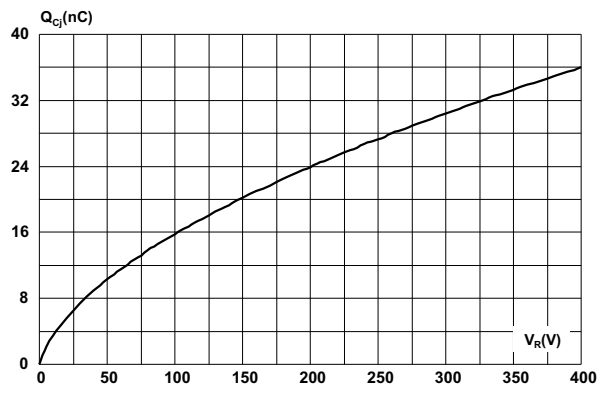


Figure 8. Total capacitive charges versus reverse voltage applied (typical values)



2 Package information

- Epoxy meets UL94, V0
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.7 N·m
- Cooling method: conduction (C)

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2.1 TO-220AC package information

Figure 9. TO-220AC package outline

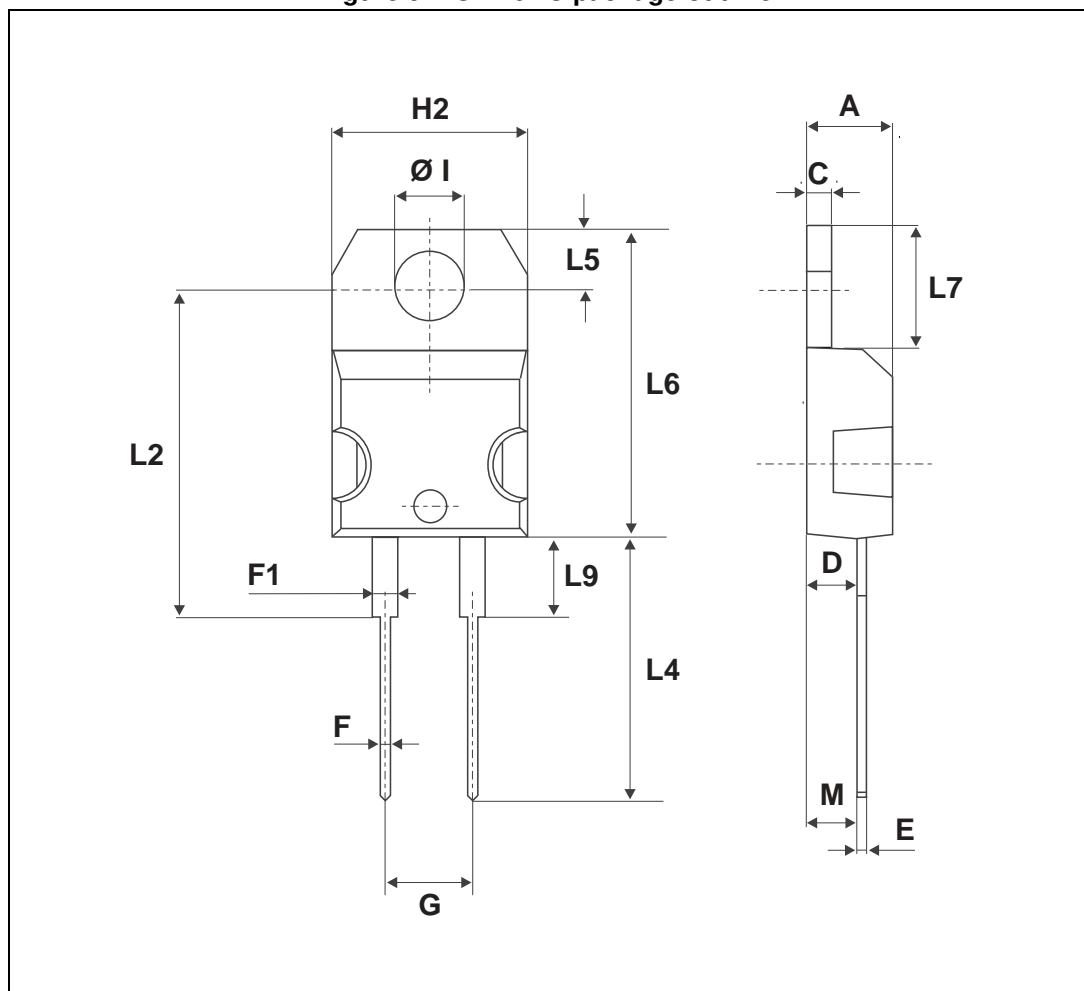


Table 6. TO-220AC package mechanical data

| Ref. | Dimensions | | | |
|---------|-------------|-------|------------|-------|
| | Millimeters | | Inches | |
| | Min. | Max. | Min. | Max. |
| A | 4.40 | 4.60 | 0.173 | 0.181 |
| C | 1.23 | 1.32 | 0.048 | 0.051 |
| D | 2.40 | 2.72 | 0.094 | 0.107 |
| E | 0.49 | 0.70 | 0.019 | 0.027 |
| F | 0.61 | 0.88 | 0.024 | 0.034 |
| F1 | 1.14 | 1.70 | 0.044 | 0.066 |
| G | 4.95 | 5.15 | 0.194 | 0.202 |
| H2 | 10.00 | 10.40 | 0.393 | 0.409 |
| L2 | 16.40 typ. | | 0.645 typ. | |
| L4 | 13.00 | 14.00 | 0.511 | 0.551 |
| L5 | 2.65 | 2.95 | 0.104 | 0.116 |
| L6 | 15.25 | 15.75 | 0.600 | 0.620 |
| L7 | 6.20 | 6.60 | 0.244 | 0.259 |
| L9 | 3.50 | 3.93 | 0.137 | 0.154 |
| M | 2.6 typ. | | 0.102 typ. | |
| Diam. I | 3.75 | 3.85 | 0.147 | 0.151 |

3 Ordering information

Table 7. Ordering information

| Order code | Marking | Package | Weight | Base qty | Delivery mode |
|--------------|------------|----------|--------|----------|---------------|
| STPSC12H065D | PSC12H065D | TO-220AC | 1.86 g | 50 | Tube |

4 Revision history

Table 8. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 27-Nov-2014 | 1 | First issue. |
| 13-Jul-2015 | 2 | Removed D ² PAK package information and updated Table 7 . |

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